

# BC372, BC373

## High Voltage Darlington Transistors

### NPN Silicon

#### Features

- Pb-Free Packages are Available\*

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	$V_{CEO}$	100 80	Vdc
Collector–Base Voltage	$V_{CES}$	100 80	Vdc
Emitter–Base Voltage	$V_{EBO}$	12	Vdc
Collector Current – Continuous	$I_C$	1.0	Adc
Total Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above $T_A = 25^\circ\text{C}$	$P_D$	625 5.0	mW mW/°C
Total Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above $T_A = 25^\circ\text{C}$	$P_D$	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	-55 to +150	°C

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction–to–Case	$R_{\theta JC}$	83.3	°C/W

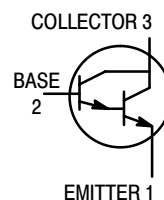
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

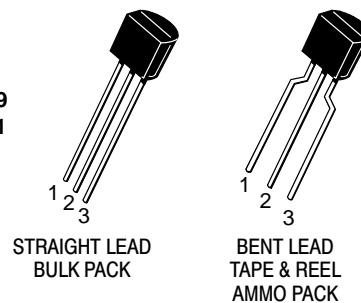


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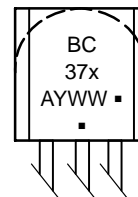
<http://onsemi.com>



TO-92  
CASE 29  
STYLE 1



#### MARKING DIAGRAM



x = 2 or 3  
A = Assembly Location  
Y = Year  
WW = Work Week  
▪ = Pb-Free Package  
(Note: Microdot may be in either location)

#### ORDERING INFORMATION

Device	Package	Shipping†
BC372G	TO-92 (Pb-Free)	5000 Units / Bulk
BC373RL1	TO-92	2000 / Tape & Reel
BC373RL1G	TO-92 (Pb-Free)	2000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit	
<b>OFF CHARACTERISTICS</b>						
Collector–Emitter Breakdown Voltage <sup>(1)</sup> (I <sub>C</sub> = 100 μAdc, I <sub>B</sub> = 0)	BC372 BC373	V <sub>(BR)CES</sub>	100 80	– –	– –	Vdc
Collector–Base Breakdown Voltage (I <sub>C</sub> = 100 μAdc, I <sub>E</sub> = 0)	BC372 BC373	V <sub>(BR)CBO</sub>	100 80	– –	– –	Vdc
Emitter–Base Breakdown Voltage (I <sub>E</sub> = 10 μAdc, I <sub>C</sub> = 0)		V <sub>(BR)EBO</sub>	12	–	–	Vdc
Collector Cutoff Current (V <sub>CB</sub> = 80 Vdc, I <sub>E</sub> = 0) (V <sub>CB</sub> = 60 Vdc, I <sub>E</sub> = 0)	BC372 BC373	I <sub>CBO</sub>	– –	– –	100 100	nAdc
Emitter Cutoff Current (V <sub>EB</sub> = 10 V, I <sub>C</sub> = 0)		I <sub>EBO</sub>	–	–	100	nAdc

## ON CHARACTERISTICS (Note 1)

DC Current Gain (I <sub>C</sub> = 250 mAdc, V <sub>CE</sub> = 5.0 Vdc) (I <sub>C</sub> = 100 mAdc, V <sub>CE</sub> = 5.0 Vdc)		h <sub>FE</sub>	8.0 10	– –	– 160	K
Collector–Emitter Saturation Voltage (I <sub>C</sub> = 250 mAdc, I <sub>B</sub> = 0.25 mAdc)		V <sub>CE(sat)</sub>	–	1.0	1.1	Vdc
Base–Emitter Saturation Voltage (I <sub>C</sub> = 250 mAdc, I <sub>B</sub> = 0.25 mAdc)		V <sub>BE(sat)</sub>	–	1.4	2.0	Vdc

## DYNAMIC CHARACTERISTICS

Current–Gain Bandwidth Product (I <sub>C</sub> = 100 mAdc, V <sub>CE</sub> = 5.0 Vdc, f = 100 MHz)		f <sub>T</sub>	100	200	–	MHz
Output Capacitance (V <sub>CB</sub> = 10 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)		C <sub>ob</sub>	–	10	25	pF
Noise Figure (I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 5.0 Vdc, R <sub>g</sub> = 100 kΩ, f = 1.0 kHz)		NF	–	2.0	–	dB

1. Pulse Test: Pulse Width = 300 μs, Duty Cycle 2.0%.

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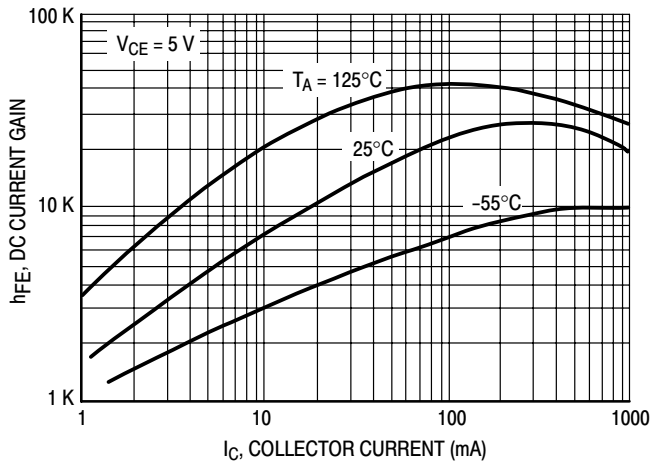


Figure 1. DC Current Gain

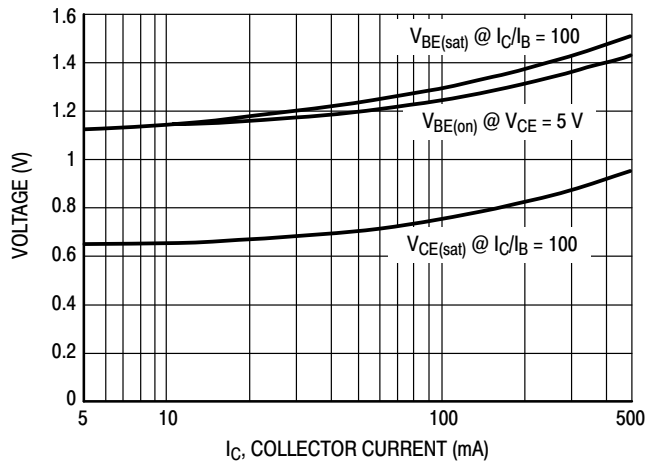


Figure 2. "Saturation" and "On" Voltages

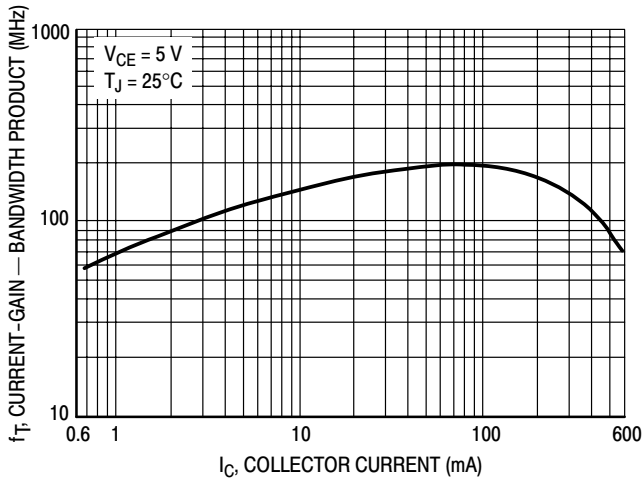


Figure 3. Current-Gain — Bandwidth Product

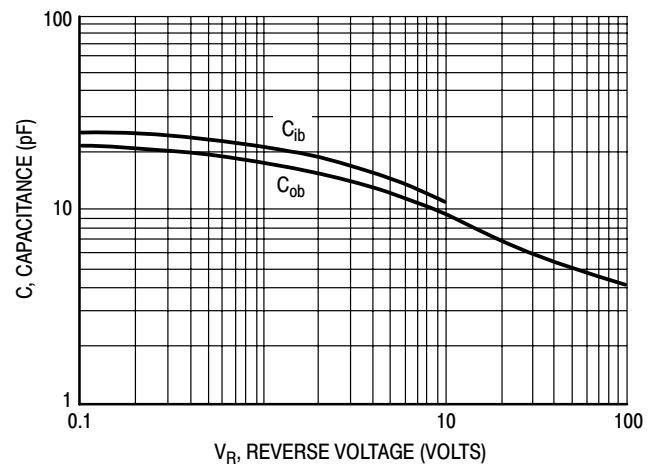


Figure 4. Capacitances

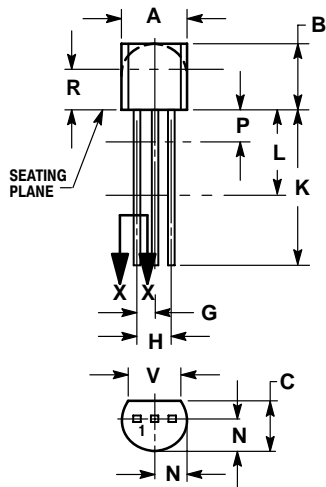
# BC372, BC373

## PACKAGE DIMENSIONS

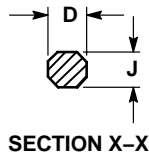
### TO-92 (TO-226)

CASE 29-11

ISSUE AM



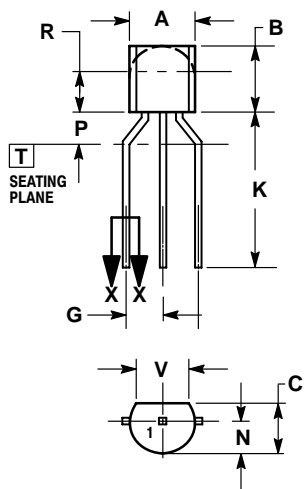
STRAIGHT LEAD  
BULK PACK



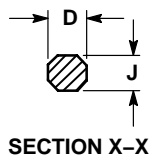
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---



BENT LEAD  
TAPE & REEL  
AMMO PACK



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	MILLIMETERS	
	MIN	MAX
A	4.45	5.20
B	4.32	5.33
C	3.18	4.19
D	0.40	0.54
G	2.40	2.80
J	0.39	0.50
K	12.70	---
N	2.04	2.66
P	1.50	4.00
R	2.93	---
V	3.43	---

STYLE 1:

1. EMITTER
2. BASE
3. COLLECTOR

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